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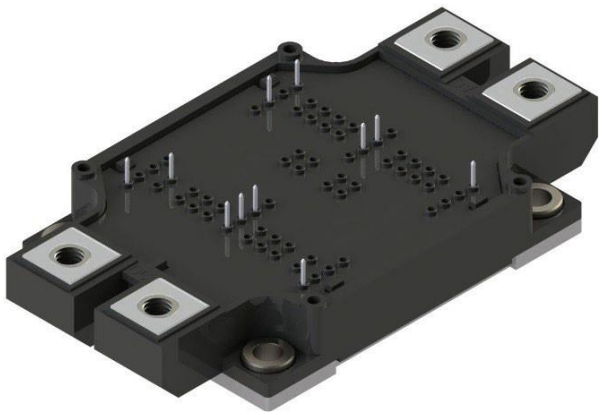
1200V/600A Half Bridge SiC MOSFET Module

PRXS600HF12I3C2



Description

The PRXS600HF12I3C2 is a Half Bridge SiC MOSFET Power Module. It integrates high performance SiC MOSFET chips designed for the applications such as Motor drives and Renewable energy.

Features

- 1200V/3.6mΩ (V_{GS} = 15V), 3.2mΩ (V_{GS} = 18V)
- Low thermal resistance with Si_3N_4 AMB
- 175°C maximum junction temperature
- Low inductive design
- Thermistor inside
- Pressfit terminal
- Copper base size: 79mm*62mm

Applications

- xEV Applications
- Motor Drive
- Vehicle Fast Chargers
- Renewable energy

Circuit Diagram

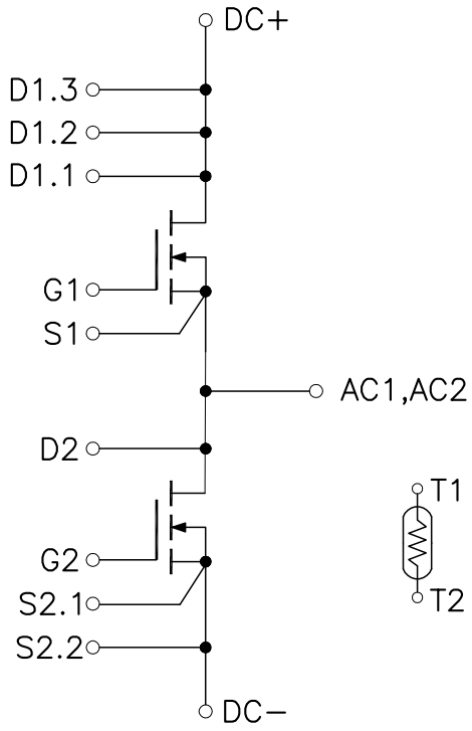


Figure 1. Out drawing & circuit diagram for PRXS600HF12I3C2

Note: Please use **S2.1** for the low side drive signal and do not connect it to **S2.2** which is power terminal

Pin Configuration and Marking Information

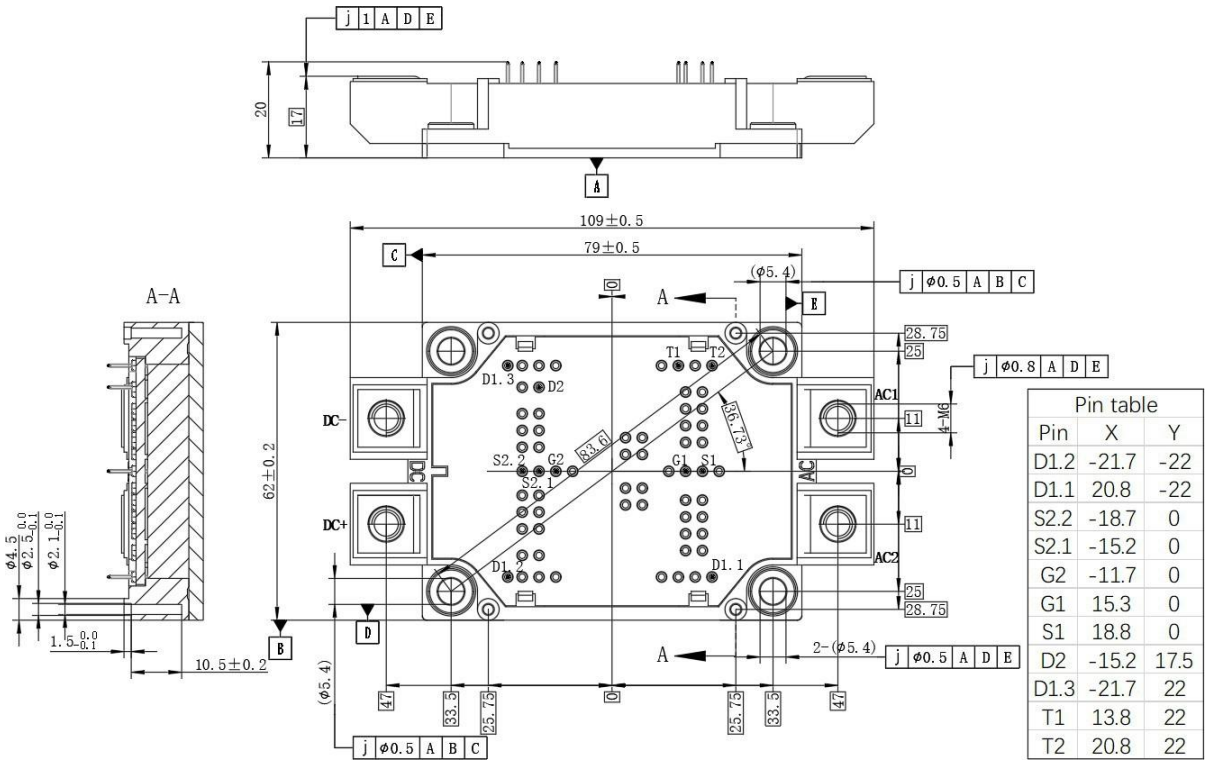


Figure 2. Pin configuration

Module

Parameter	Conditions	Value	Unit
Isolation Voltage	RMS, f =50Hz, t =1min	3.4	KV
Material of module baseplate	-	Cu	-
Creepage distance	terminal to heatsink terminal to terminal	14.5 10	mm
Clearance	terminal to heatsink terminal to terminal	12.5 10	mm
CTI	-	>400	-
Module lead resistance, terminals – chip	T_C =25°C	0.3	mΩ
Mounting torque for module mounting	M5, M6	3 to 6	Nm
Weight	-	250	g

PRXS600HF12I3C2
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Maximum Ratings (T_j = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-Source Voltage	G-S Short	1200	V
V_{GSS}	Gate-Sourse Voltage	D-S Short, AC frequency ≥1Hz, Note1	-10 to 22	V
I_{DS}	DC Continuous Drain Current	T_f =25°C , V_{GS} =+15V	630	A
I_{DS}	DC Continuous Drain Current	T_f =65°C , V_{GS} =+15V	540	A
I_{SD}	Source (Body diode) Current	T_f =25°C, with ON signal	630	A
I_{SD}	Source (Body diode) Current	T_f =65°C, with ON signal	540	A
I_{DSM}	Pulse Drain Current	T_C =65°C, Pulse width =1ms, V_{GS} =+15V, Note2	1200	A
P_{tot}	Total Power Dissipation	T_C =25°C	2585	W
T_{jmax}	Max Junction Temperature	-	175	°C
T_{stg}	Storage Temperature	-	-40 to 125	°C

Note1: Recommended Operating Value, +18V/-5V, +15V/-4V
Note2: Pulse width limited by maximum junction temperature

NTC characteristics

Symbol	Parameter	Condition	Value			Unit
			Min.	Typ.	Max.	
R_{25}	Resistance	T_c =25°C	-	5	-	kΩ
ΔR/R	Deviation of R100	T_c =100°C, R_{100} =493Ω	5	-	5	%
P_{25}	Power dissipation	T_c =25°C	-	-	20	mW
$B_{25/50}$	B-value	R2 =R25 exp [$B_{25/50}$(1/T2 - 1/(298,15 K))]	-	3375	-	K
$B_{25/80}$	B-value	R2 =R25 exp [$B_{25/80}$(1/T2 - 1/(298,15 K))]	-	3411	-	K
$B_{25/100}$	B-value	R2 =R25 exp [$B_{25/100}$(1/T2 - 1/(298,15 K))]	-	3433	-	K

MOSFET Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} =0V, I_D =600uA		1200	-	-	V
I_{DSS}	Zero gate voltage drain Current	V_{DS} =1200V, V_{GS} =0V		-	6	-	μA
$V_{GS(th)}$	Gate-source threshold Voltage	I_D =210mA, V_{DS} = V_{GS}	T_j =25°C	1.8	2.7	–	V
I_{GSS}	Gate-Source Leakage Current	V_{GS} =20V, V_{DS} =0V	T_j =25°C	-	-	600	nA
$R_{DS(on)}$ (Chip)	Static drain-source On-state resistance	I_D =600A, V_{GS} =+15V	T_j =25°C	-	3.6	5.0	mΩ
			T_j =175°C	–	5.2	–	mΩ
		I_D =600A, V_{GS} =+18V	T_j =25°C	–	3.2	–	mΩ
			T_j =175°C	–	4.4	–	mΩ
$V_{DS(on)}$ (Chip)	Static drain-source On-state Voltage	I_D =600A, V_{GS} =+15V	T_j =25°C	–	2.16	3.0	V
			T_j =175°C	–	3.12	–	V
		I_D =600A, V_{GS} =+18V	T_j =25°C	–	1.92	–	V
			T_j =175°C	–	2.64	–	V
C_{iss}	Input Capacitance	V_D =800V, V_{GS} =0V, f =100KHz		-	34.8	-	nF
C_{oss}	Output Capacitance			-	1.06	-	nF
C_{rss}	Reverse transfer Capacitance			-	0.086	-	nF
Q_g	Total gate charge	V_{DD} =800V, I_D =360A, V_{GS} =+15/−5V		-	1080	-	nC
$t_{d(on)}$	Turn-on delay time	V_{DD} =600V, I_D =600A, V_{GS} =+15/-4V, R_{gon}/R_{goff} =5.1/3.3Ω, Inductive load switching operation	T_j =25°C	-	49	-	ns
			T_j =150°C	-	46	-	
t_r	Rise time		T_j =25°C	-	30	-	ns
			T_j =150°C	-	24	-	
$t_{d(off)}$	Turn-off delay time		T_j =25°C	-	112	-	ns
			T_j =150°C	-	123	-	
t_f	Fall time		T_j =25°C	-	17	-	ns
			T_j =150°C	-	441	-	
E_{on}	Turn-on power dissipation		T_j =25°C	-	28.8	-	mJ
			T_j =150°C	-	26.8	-	
E_{off}	Turn-off power dissipation		T_j =25°C	-	12.4	-	mJ
			T_j =150°C	-	13.8	-	
$R_{th(j-c)}$	FET Thermal Resistance	Junction to Case		-	0.058	-	K/W
$R_{th(c-f)}$	Contact thermal Resistance	With thermal conductive grease, Note3		-	0.015	-	K/W

Note3: Assumes Thermal Conductivity of grease is 0.9W/m・K and thickness is 50um.

Body Diode Electrical characteristics (T_j =25°C unless otherwise specified, chip)

Symbol	Item	Condition		Value			Unit
				Min.	Typ.	Max	
V_{SD}	Body Diode Forward Voltage	V_{GS} =-5V, I_{SD} =600A	T_j =25°C	-	5.2	-	V
			T_j =175°C	-	4.3	-	
T_{rr}	Reverse recovery time	V_{DD} =600V, I_D =600A, V_{GS} =+15/-4V, R_{gon}/R_{goff} =5.1/3.3Ω, Inductive load switching operation	T_j =25°C	-	26	-	ns
			T_j =150°C	-	49	-	
Q_{rr}	Reverse recovery charge		T_j =25°C	-	2.3	-	µC
			T_j =150°C	-	9.6	-	
E_{rr}	Diode switching power dissipation		T_j =25°C	-	1.15	-	mJ
			T_j =150°C	-	4.12	-	

Test Conditions

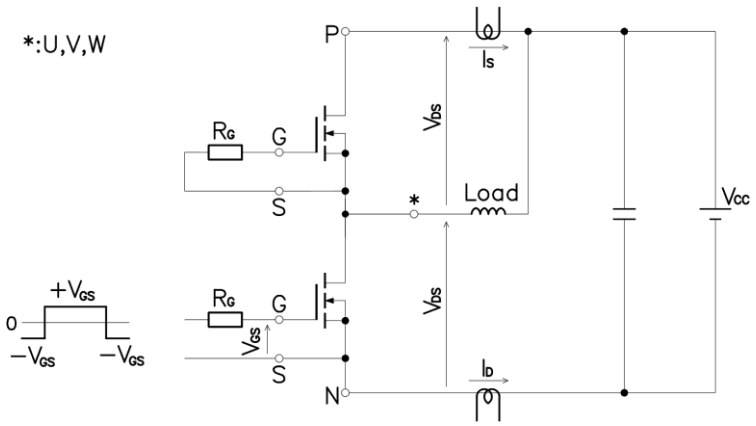

Figure 3. Switching time measure circuit

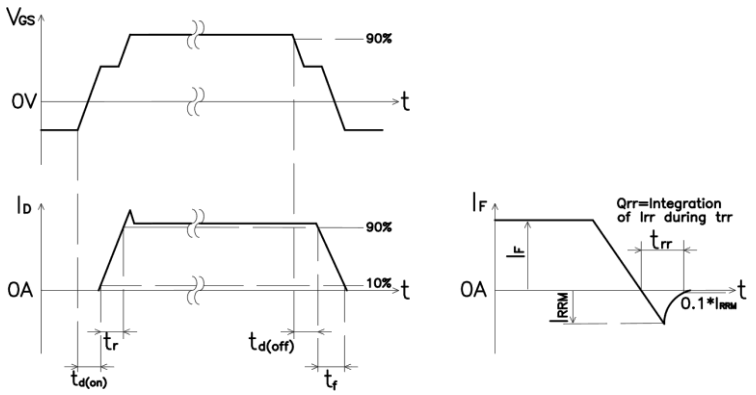

Figure 4. Switching time definition

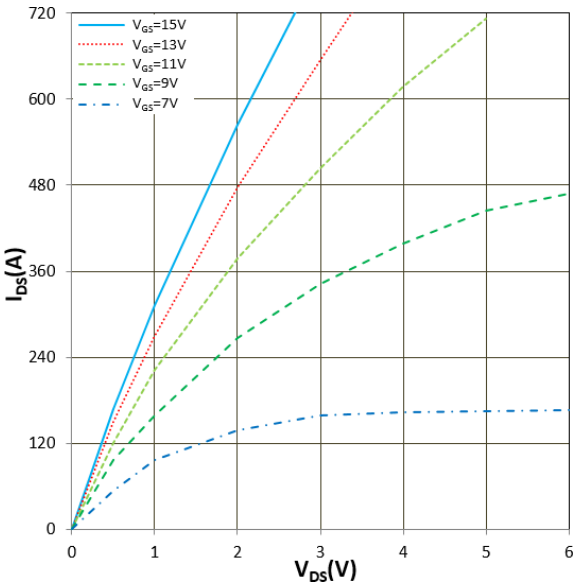

Figure 5. I_{DS} vs V_{DS}
T_j =25°C

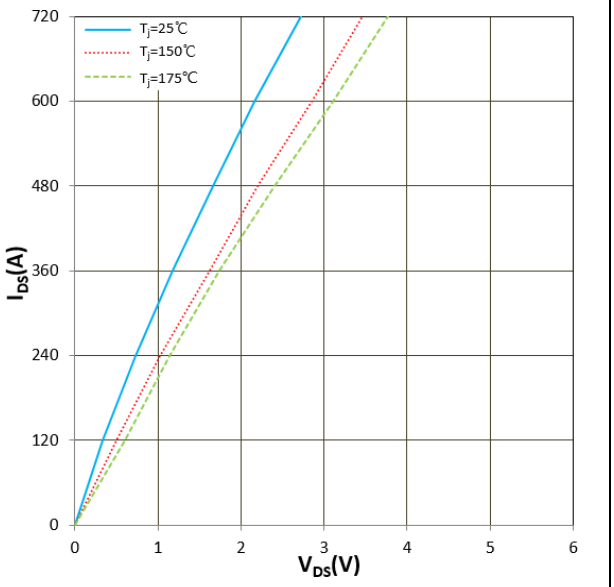

Figure 6. I_{DS} vs V_{DS}
V_{GS} =+15V

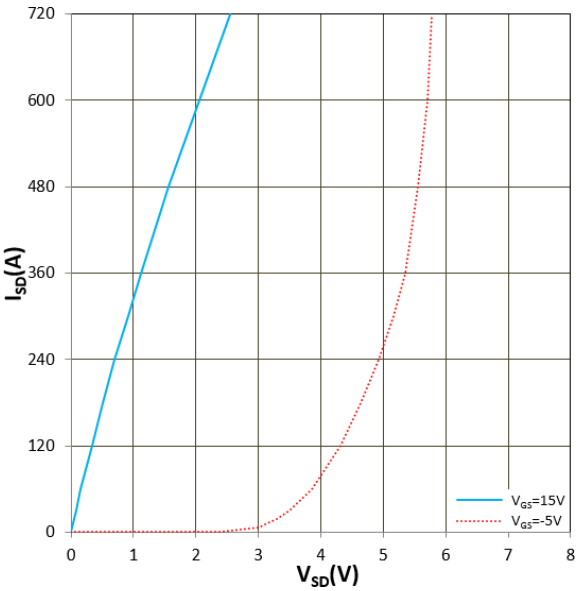

Figure 7. I_{SD} vs V_{SD} (V_F)
T_j =25°C

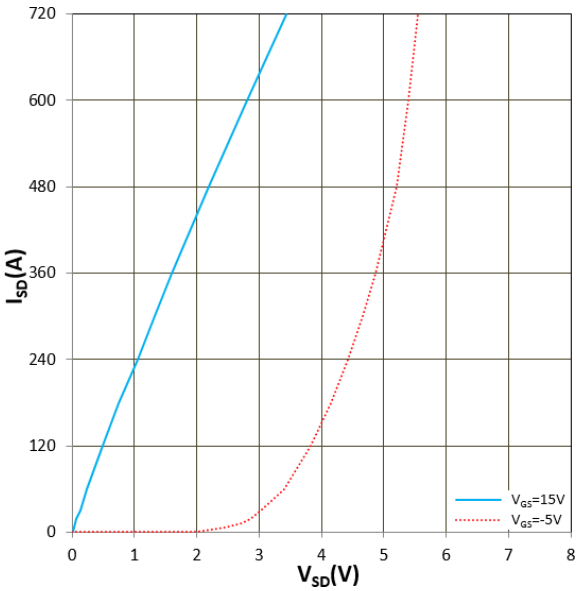

Figure8. I_{SD} vs V_{SD} (V_F)
T_j =175°C

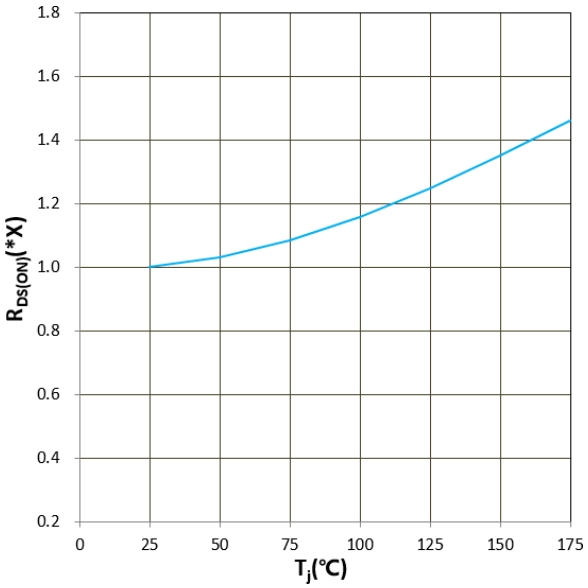

Figure 9. $R_{DS(ON)}$ vs T_j
V_{GS} =+15V, I_D =600A, 1.0X =3.6mΩ

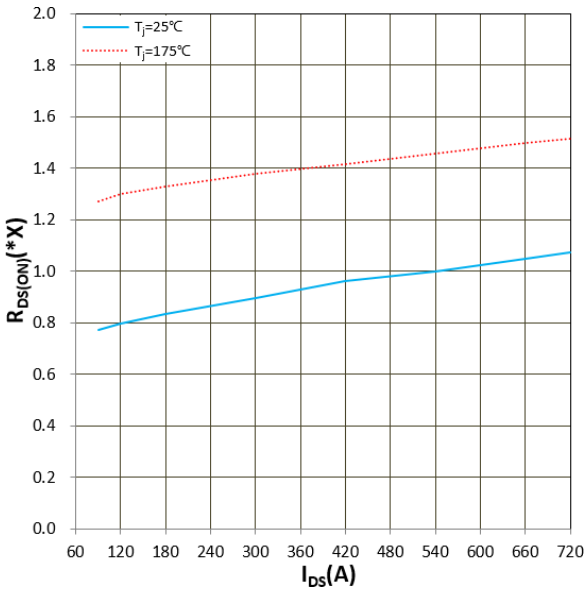

Figure 10. $R_{DS(ON)}$ vs I_{DS}
V_{GS} =+15V, I_D =600A, 1.0X =3.6mΩ

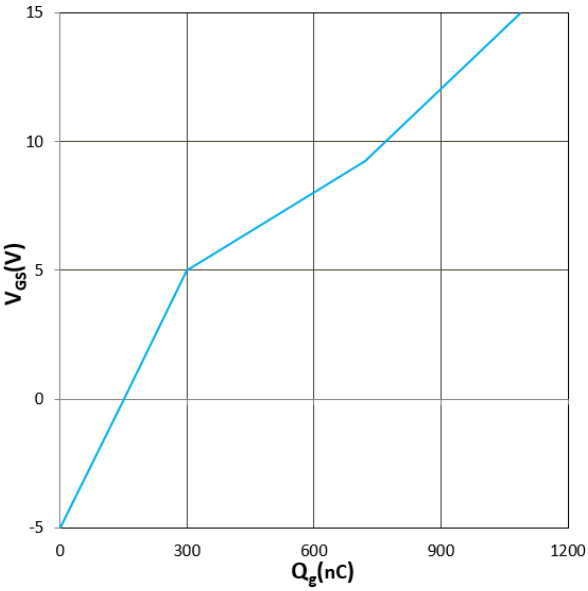

Figure 11. V_{GS} vs Q_g
V_{DS} =800V, I_D =360A, T_j =25℃

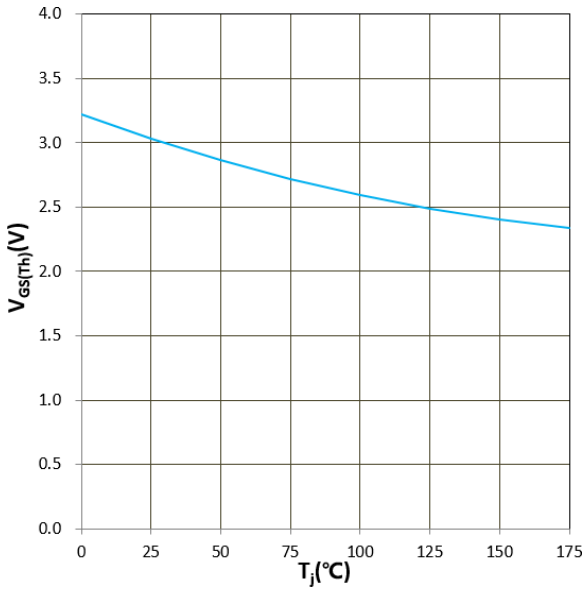

Figure 12. $V_{GS(TH)}$ vs T_j
V_{GS} =V_{DS}, I_D =210mA

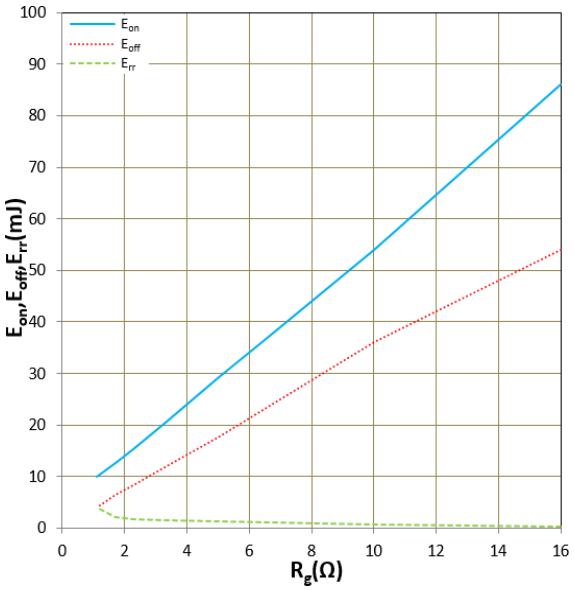

Figure 13. E_{on}, E_{off}, E_{rr} vs R_g
T_j =25°C, V_{CC} =600V, V_{GS} =+15V/-4V, I_D =600A
Inductive Load

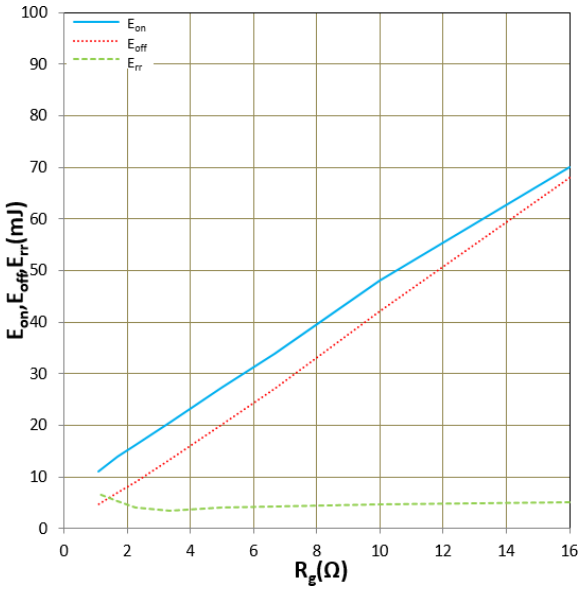

Figure 14. E_{on}, E_{off}, E_{rr} vs R_g
T_j =150°C, V_{CC} =600V, V_{GS} =+15V/-4V, I_D =600A
Inductive Load

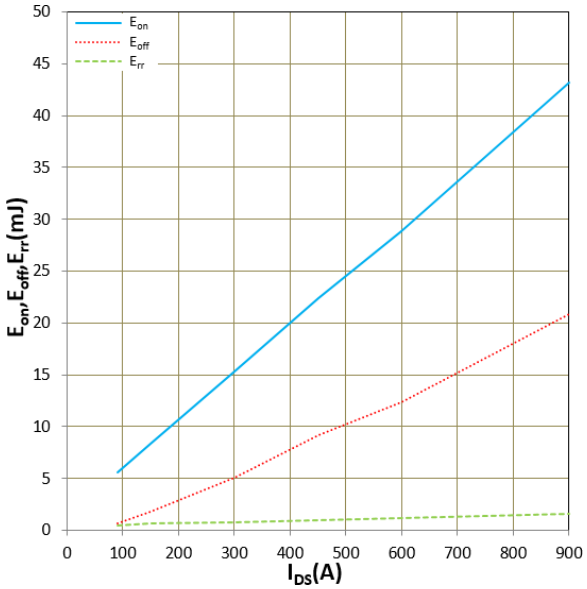

Figure 15. E_{on}, E_{off}, E_{rr} vs I_{DS}
T_j =25°C, V_{CC} =600V, V_{GS} =+15V/-4V
R_{gon}/R_{goff} =5.1/3.3Ω, Inductive Load

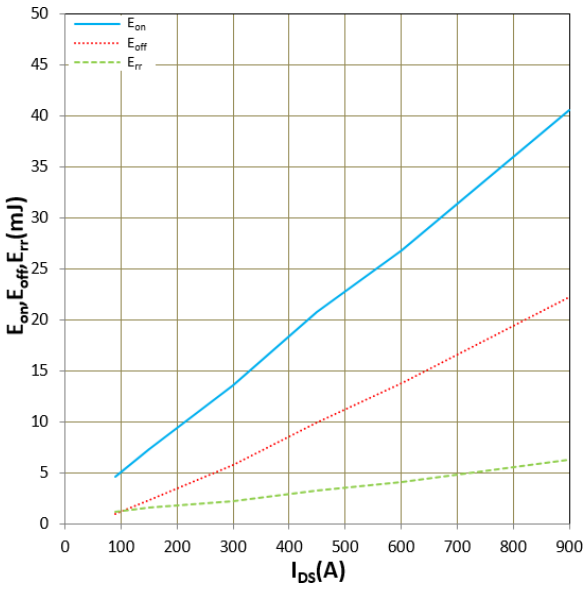

Figure 16. E_{on}, E_{off}, E_{rr} vs I_{DS}
T_j =150°C, V_{CC} =600V, V_{GS} =+15V/-4V
R_{gon}/R_{goff} =5.1/3.3Ω, Inductive Load